



OVERVIEW

The SM5022 series are crystal oscillator module ICs fabricated in NPC's Molybdenum-gate CMOS, that incorporate high-frequency, low current consumption oscillator and output buffer circuits. Feedback resistors and high-frequency capacitors are built-in, eliminating the need for external components to make a stable fundamental oscillator.

FEATURES

- Up to 30MHz operating frequency range (fundamental oscillation)
- Oscillator capacitors C_G, C_D built-in (excluding A2A, A4A)
- Inverter amplifier feedback resistor built-in
- TTL input level
- Output drive capability
 - $4\text{mA} (V_{DD} = 2.7\text{V})$
 - $8mA (V_{DD} = 4.5V)$

- Output three-state function
- Operating supply voltage range
 - 2.7 to 5.5V (A×A series)
 - 4.5 to 5.5V (B×A series)
- f_O, f_O/2, f_O/4, f_O/8 output frequency, determined by internal connection
- 6-pin SOT (SM5022××AH)
- Chip form (CF5022××A)

SERIES CONFIGURATION

Version*1		g supply ange [V]	operating	mended frequency ² [MHz]	capac	lt-in itance F]	gm	Rf [kΩ]	Output	Output	Output	Standb	y mode				
version	Chip	SOT	3V operation	5V operation	C _G	C _D	ratio		frequency	level	Oscillator stop function	Output state					
SM5022A1AH			4 to 24	4 to 04	4 to 04	4 to 04	4 to 04	4 to 04		8	10			fo			
SM5022A2AH			4 10 24		-	-	1 600		fo								
SM5022A3AH	2.7 to 5.5	2.7 to 5.5		4 to 30	8 10	10		fo/2	CMOS	Yes	Hi-Z						
SM5022A4AH	2.7 10 5.5	2.7 10 5.5	4 to 30	4 10 30		-		fo/2									
SM5022A5AH			4 10 30		8	10			fo/4								
SM5022A7AH					8	10			fo/8								
SM5022B1AH	4.5 to 5.5	4.5 to 5.5	×	4 to 30	8	10	1	600	fo	TTL	Yes	Hi-Z					

^{*1.} Chip form devices have designation CF5022××.

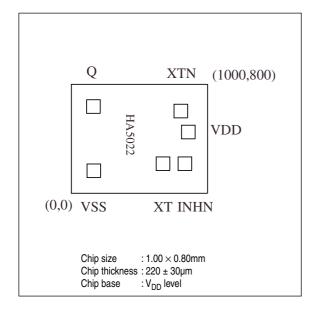
ORDERING INFORMATION

Device	Package
SM5022××AH	SOT23-6
CF5022××A-2	Chip form

^{*2.} The recommended operating frequency is a yardstick value derived from the crystal used for NPC characteristics authentication. However, the oscillator frequency band is not guaranteed. Specifically, the characteristics can vary greatly due to crystal characteristics and mounting conditions, so the oscillation characteristics of components must be carefully evaluated.

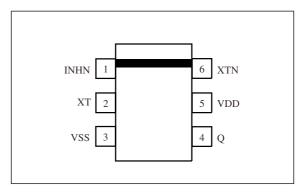
PAD LAYOUT

(Unit: μm)



PINOUT

(Top view)



Version	Product ID
SM5022A1AH	A00
SM5022A2AH	A01
SM5022A3AH	A02
SM5022A4AH	A03
SM5022A5AH	A04
SM5022A7AH	A05
SM5022B1AH	A06

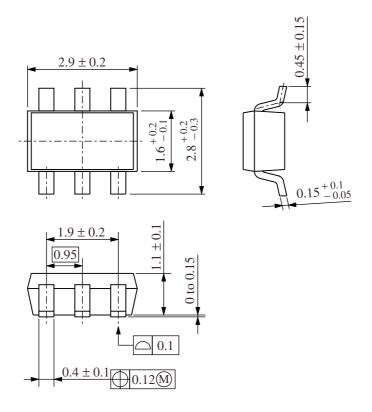
PIN DESCRIPTION and PAD DIMENSIONS

Normalian	Number Name I			Pad dimensions [µm]		
Number	Name	I/O		Description	х	Y
1	INHN	I	Output state control	Output state control input. High impedance when LOW. Pull-up resistor built in		217
2	XT	I	Amplifier input. Crystal oscillator connection pins. Crystal oscillator is connected between XT and XTN		637	217
3	VSS	-	Ground		165	165
4	Q	0	Output. Output frequ	uency (f _O , f _O /2, f _O /4, f _O /8) determined by internal connection	162	637
5	VDD	-	Supply voltage		859	450
6	XTN	0	Amplifier output. Crystal oscillator connection pins. Crystal oscillator is connected between XT and XTN		804	604

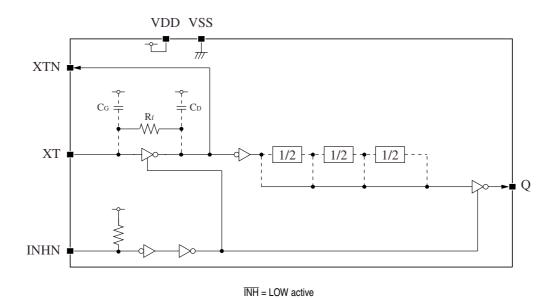
PACKAGE DIMENSIONS

(Unit: mm)

• 6-pin SOT



BLOCK DIAGRAM



SPECIFICATIONS

Absolute Maximum Ratings

 $V_{SS} = 0V$

Parameter	Symbol	Condition	Rating	Unit	
Supply voltage range	V _{DD}		- 0.5 to + 7.0	V	
Input voltage range	V _{IN}		- 0.5 to V _{DD} + 0.5	V	
Output voltage range	V _{OUT}		- 0.5 to V _{DD} + 0.5	V	
Operating temperature range	T _{opr}		- 40 to + 85	°C	
Ctorogo tomporatura rango		Chip form	- 65 to + 150	۰,0	
Storage temperature range	T _{stg}	SOT23-6	- 55 to + 125	°C	
Output current	I _{OUT}		13	mA	
Power dissipation	P _D	SOT23-6	250	mW	

Recommended Operating Conditions

3V operation: A×A series

 $V_{SS} = 0V$, $f \le 30MHz$, $C_L \le 15pF$

Parameter	Symbol	Condition		Unit		
	Symbol	min	typ	max	Onn	
Supply voltage	V_{DD}		2.7	-	3.6	V
Input voltage	V _{IN}		V _{SS}	-	V _{DD}	V
Operating temperature	T _{OPR}		- 20	-	+ 80	°C

5V operation: A×A series/ B×A series

 $V_{SS} = 0V$, $f \le 30MHz$, $C_L \le 15pF$

Parameter	Symbol Condit	Condition		Unit		
		Condition	min	typ	max	Oill
Supply voltage	V_{DD}		4.5	-	5.5	V
Input voltage	V _{IN}		V _{SS}	-	V _{DD}	V
Operating temperature	T _{OPR}		- 20	-	+ 80	°C

Electrical Characteristics

3V operation: A×A series

 $V_{\rm DD}$ = 2.7 to 3.6V, $V_{\rm SS}$ = 0V, Ta = - 20 to + 80°C unless otherwise noted.

Downwater	Compleal	Symbol Condition			Rating		
Parameter	Symbol	Condit	min	typ	max	Unit	
HIGH-level output voltage	V _{OH}	Q: Measurement cct 1, V _{DD} = 2.7V	, I _{OH} = 4mA	2.1	2.4	-	٧
LOW-level output voltage	V _{OL}	Q: Measurement cct 2, V _{DD} = 2.7V, I _{OL} = 4mA		-	0.3	0.4	٧
HIGH-level input voltage	V _{IH}	INHN		2.0	-	-	٧
LOW-level input voltage	V _{IL}	INHN		-	-	0.5	٧
Outrot lealer as somet		Q: Measurement cct 2, V _{DD} = 3.6V, INHN = LOW, V _{OH} = V _{DD}			-	10	
Output leakage current	Ι _Ζ	Q: Measurement cct 2, V_{DD} = 3.6V, INHN = LOW, V_{OL} = V_{SS}			-	10	μA
Current consumption	I _{DD}	30MHz crystal oscillator, measurer INHN = open, C _L = 15pF	nent cct 3, load cct 1,	-	4	7	mA
INHN pull-up resistance	R _{UP}	Measurement cct 4		25	100	250	kΩ
Feedback resistance	R _f	Measurement cct 5		200	600	1000	kΩ
	C _G		SM5022A1AH, CF5022A1A	7.44	8	8.56	pF
Built-in capacitance	C _D	Design value. A monitor pattern on a wafer is tested.	SM5022A3AH, CF5022A3A SM5022A5AH, CF5022A5A SM5022A7AH, CF5022A7A	9.3	10	10.7	pF

5V operation: $A \times A$, $B \times A$ series

 $V_{DD} = 4.5$ to 5.5V, $V_{SS} = 0$ V, Ta = -20 to +80°C unless otherwise noted.

Parameter	Complete	Condition -			Rating		
Parameter	Symbol				typ	max	Unit
HIGH-level output voltage	V _{OH}	Q: Measurement cct 1, V _{DD} = 4.5V	, I _{OH} = 8mA	3.9	4.2	-	٧
LOW-level output voltage	V _{OL}	Q: Measurement cct 2, V _{DD} = 4.5V	, I _{OL} = 8mA	-	0.3	0.4	٧
HIGH-level input voltage	V _{IH}	INHN		2.0	-	-	٧
LOW-level input voltage	V _{IL}	INHN		-	-	0.8	٧
Outrot lealing a surrent		Q: Measurement cct 2, V _{DD} = 5.5V	Measurement cct 2, V_{DD} = 5.5V, INHN = LOW, V_{OH} = V_{DD}		-	10	
Output leakage current	I _Z	Q: Measurement cct 2, V _{DD} = 5.5V, INHN = LOW, V _{OL} = V _{SS}			-	10	μA
	I _{DD}	30MHz crystal oscillator, measurement cct 3, load cct 1, INHN = open, C _L = 15pF	SM5022A×AH, CF5022A×A	-	7	12	
Current consumption		30MHz crystal oscillator, measurement cct 3, load cct 2, INHN = open, C _L = 15pF	SM5022B×AH, CF5022B×A	-	7	12	- mA
INHN pull-up resistance	R _{UP}	Measurement cct 4		25	100	250	kΩ
Feedback resistance	R _f	Measurement cct 5		200	600	1000	kΩ
	C _G		SM5022A1AH, CF5022A1A	7.44	8	8.56	pF
Built-in capacitance	C _D	on a wafer is tested.	SM5022A3AH, CF5022A3A SM5022A5AH, CF5022A5A SM5022A7AH, CF5022A7A SM5022B1AH, CF5022B1A	9.3	10	10.7	pF

Switching Characteristics

CMOS Output Version: A×A series

3V operation

 $V_{\rm DD}$ = 2.7 to 3.6V, $V_{\rm SS}$ = 0V, Ta = - 20 to + 80°C unless otherwise noted.

Parameter	Cumbal	Condition			Rating			
Parameter	Symbol	Conditio	min	typ	max	Unit		
Output rise time		Measurement cct 6, load cct 1, C _L = 15pF	0.2V _{DD} to 0.8V _{DD}	-	5	10	no	
	t _{r1}		0.1V _{DD} to 0.9V _{DD}	-	10	20	ns	
0	t _{f1}	Measurement cct 6, load cct 1, C _L = 15pF	0.8V _{DD} to 0.2V _{DD}	-	5	10	ns	
Output fall time			0.9V _{DD} to 0.1V _{DD}	-	10	20		
Output duty cycle*1	Duty	Measurement cct 6, load cct 1, V _{DD} = f = 30MHz	Measurement cct 6, load cct 1, V _{DD} = 3V, Ta = 25°C, C _L = 15pF,		-	55	%	
Output disable delay time*2	t _{PLZ}	Macaurament act 7 load act 1 V	Weasurement cct 7, load cct 1, V _{DD} = 3V, Ta = 25°C, C _L = 15pF		-	100	ns	
Output enable delay time*2	t _{PZL}	1 ivieasurement cct 7, load cct 1, V _{DD} =	: 3 V, 14 = 23 U, UL = 15pr	-	-	100	ns	

^{*1.} The duty cycle characteristic is checked the sample chips of each production lot.

5V operation

 $V_{DD} = 4.5$ to 5.5V, $V_{SS} = 0$ V, Ta = -20 to +80°C unless otherwise noted.

Parameter	Symbol	Condition		Unit		
	Syllibol	ndoi Condition		typ	max	Ullit
Output rise time	t _{r2}	Measurement cct 6, load cct 1, 0.1V _{DD} to 0.9V _{DD} , C _L = 15pF	-	3.5	7	ns
Output fall time	t _{f2}	Measurement cct 6, load cct 1, 0.9V _{DD} to 0.1V _{DD} , C _L = 15pF	-	3.5	7	ns
Output duty cycle*1	Duty	Measurement cct 6, load cct 1, V_{DD} = 5V, Ta = 25°C, C_L = 15pF, f = 30MHz	45	-	55	%
Output disable delay time*2	t _{PLZ}	Measurement cct 7, load cct 1, V _{DD} = 5V, Ta = 25°C, C _L = 15pF	i	-	100	ns
Output enable delay time*2	t _{PZL}	weasurement cct 7, load cct 1, V _{DD} = 5v, 1a = 25 C, C _L = 15pr	-	-	100	ns

^{*1.} The duty cycle characteristic is checked the sample chips of each production lot.

^{*2.} Oscillator stop function is built-in. When INHN goes LOW, normal output stops. When INHN goes HIGH, normal output is not resumed until after the oscillator start-up time has elapsed.

^{*2.} Oscillator stop function is built-in. When INHN goes LOW, normal output stops. When INHN goes HIGH, normal output is not resumed until after the oscillator start-up time has elapsed.

TTL Output Version: $\mathbf{B} \times \mathbf{A}$ series

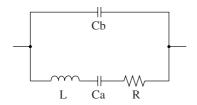
5V operation

 V_{DD} = 4.5 to 5.5V, V_{SS} = 0V, Ta = -20 to + 80° C unless otherwise noted.

Parameter	Symbol Condition			Unit		
raiailletei	Syllibol	Condition	min	typ	max	Oill
Output rise time	t _{r3}	Measurement cct 6, load cct 2, 0.4V to 2.4V, C _L = 15pF	-	2.5	7	ns
Output fall time	t _{f3}	Measurement cct 6, load cct 2, 2.4V to 0.4V, C _L = 15pF	-	2.5	7	ns
Output duty cycle*1	Duty	Measurement cct 6, load cct 2, V_{DD} = 5V, Ta = 25°C, C_L = 15pF, f = 30MHz	45	-	55	%
Output disable delay time*2	t _{PLZ}	Measurement cct 7, load cct 2, V _{DD} = 5V, Ta = 25°C, C _L = 15pF	ı	-	100	ns
Output enable delay time*2	t _{PZL}	weasurement cot 7, load cot 2, vDD = 5v, la = 25 C, CL = 15pr	-	-	100	ns

^{*1.} The duty cycle characteristic is checked the sample chips of each production lot.

Current consumption and Output waveform with NPC's standard crystal



f [MHz]	R [Ω]	L [mH]	Ca [fF]	Cb [pF]
30	17.2	4.36	6.46	2.26

FUNCTIONAL DESCRIPTION

Standby Function

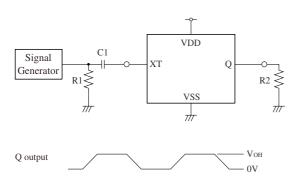
When INHN goes LOW, the oscillator output on Q goes high impedance.

INHN	Q	Oscillator
HIGH (or open)	Any f _O , f _O /2, f _O /4, or f _O /8 output frequency	Normal operation
LOW	High impedance	Stopped

^{*2.} Oscillator stop function is built-in. When INHN goes LOW, normal output stops. When INHN goes HIGH, normal output is not resumed until after the oscillator start-up time has elapsed.

MEASUREMENT CIRCUITS

Measurement cct 1



2.0Vp-p, 10MHz sine wave input signal (3V operation)

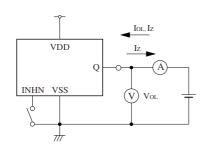
3.5Vp-p, 10MHz sine wave input signal (5V operation)

C1: 0.001μF R1: 50Ω

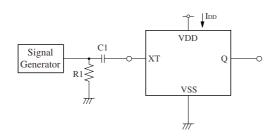
R2: 525Ω (3V operation)

490Ω (5V operation)

Measurement cct 2



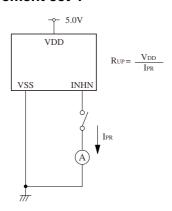
Measurement cct 3



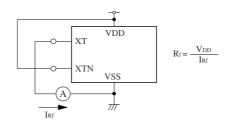
2.0Vp-p, 30MHz sine wave input signal (3V operation) 3.5Vp-p, 30MHz sine wave input signal (5V operation)

C1: 0.001μF R1: 50Ω

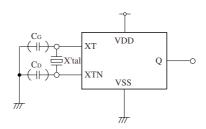
Measurement cct 4



Measurement cct 5

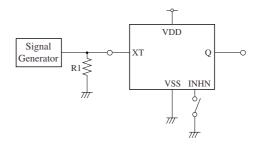


Measurement cct 6



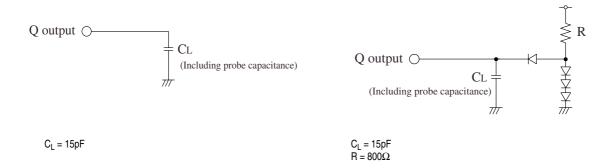
C_G ,C_D: 10pF (5022A2, 5022A4)

Measurement cct 7



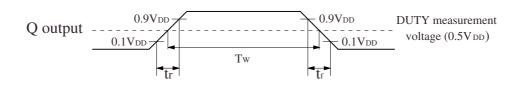
R1: 50Ω

Load cct 2

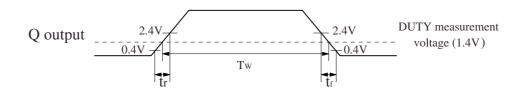


Switching Time Measurement Waveform

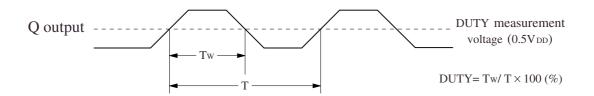
Output duty level (CMOS)



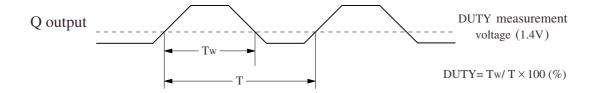
Output duty level (TTL)



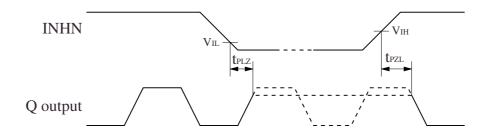
Output duty cycle (CMOS)



Output duty cycle (TTL)



Output Enable/Disable Delay



INHN input waveform $tr = tf \le 10ns$

Please pay your attention to the following points at time of using the products shown in this document.

The products shown in this document (hereinafter "Products") are not intended to be used for the apparatus that exerts harmful influence on human lives due to the defects, failure or malfunction of the Products. Customers are requested to obtain prior written agreement for such use from SEIKO NPC CORPORATION (hereinafter "NPC"). Customers shall be solely responsible for, and indemnify and hold NPC free and harmless from, any and all claims, damages, losses, expenses or lawsuits, due to such use without such agreement. NPC reserves the right to change the specifications of the Products in order to improve the characteristic or reliability thereof. NPC makes no claim or warranty that the contents described in this document dose not infringe any intellectual property right or other similar right owned by third parties. Therefore, NPC shall not be responsible for such problems, even if the use is in accordance with the descriptions provided in this document. Any descriptions including applications, circuits, and the parameters of the Products in this document are for reference to use the Products, and shall not be guaranteed free from defect, inapplicability to the design for the mass-production products without further testing or modification. Customers are requested not to export or re-export, directly or indirectly, the Products to any country or any entity not in compliance with or in violation of the national export administration laws, treaties, orders and regulations. Customers are requested appropriately take steps to obtain required permissions or approvals from appropriate government agencies.



SEIKO NPC CORPORATION

15-6, Nihombashi-kabutocho, Chuo-ku, Tokyo 103-0026, Japan Telephone: +81-3-6667-6601 Facsimile: +81-3-6667-6611 http://www.npc.co.jp/ Email: sales@npc.co.jp

NC9906CE 2006.04